## C3D10060G-Silicon Carbide Schottky Diode Z-REC ${ }^{\text {TM }}$ Rectifier

## Features

- 600-Volt Schottky Rectifier
- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- High-Frequency Operation
- Temperature-Independent Switching Behavior
- Extremely Fast Switching
- Positive Temperature Coefficient on $\mathrm{V}_{\mathrm{F}}$


## Benefits

- Replace Bipolar with Unipolar Rectifiers
- Essentially No Switching Losses
- Higher Efficiency
- Reduction of Heat Sink Requirements
- Parallel Devices Without Thermal Runaway


## Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Typical PFC Pout $_{\text {out }}$ : 1000W-2000W
- Motor Drives
- Typical Power : 3HP-5HP


## Package



TO-263-2

## Maximum Ratings

| Symbol | Parameter | Value | Unit | Test Conditions | Note |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\text {RRM }}$ | Repetitive Peak Reverse Voltage | 600 | V |  |  |
| $V_{\text {RSM }}$ | Surge Peak Reverse Voltage | 600 | V |  |  |
| $\mathrm{V}_{\mathrm{DC}}$ | DC Blocking Voltage | 600 | V |  |  |
| $\mathrm{I}_{\text {(AVG) }}$ | Average Forward Current | 10 | A | $\mathrm{T}_{\mathrm{C}}=150^{\circ} \mathrm{C}$ |  |
| $\mathrm{I}_{\text {FRM }}$ | Repetitive Peak Forward Surge Current | $\begin{aligned} & 67 \\ & 44 \end{aligned}$ | A | $\mathrm{T}_{\mathrm{c}}=25^{\circ} \mathrm{C}, \mathrm{t}_{\mathrm{p}}=10 \mathrm{~ms}$, Half Sine Wave, $\mathrm{D}=0.3$ $\mathrm{T}_{\mathrm{C}}=110^{\circ} \mathrm{C}, \mathrm{t}_{\mathrm{p}}=10 \mathrm{~ms}$, Half Sine Wave, $\mathrm{D}=0.3$ |  |
| $\mathrm{I}_{\text {FSM }}$ | Non-Repetitive Peak Forward Surge Current | $\begin{aligned} & 90 \\ & 71 \end{aligned}$ | A | $T_{c}=25^{\circ} \mathrm{C}, \mathrm{t}_{\mathrm{p}}=10 \mathrm{~ms}$, Half Sine Wave, $\mathrm{D}=0.3$ <br> $\mathrm{T}_{\mathrm{c}}=110^{\circ} \mathrm{C}, \mathrm{t}_{\mathrm{p}}=10 \mathrm{~ms}$, Half Sine Wave, $\mathrm{D}=0.3$ |  |
| $\mathrm{I}_{\text {FSM }}$ | Non-Repetitive Peak Forward Surge Current | 250 | A | $\mathrm{T}_{\mathrm{c}}=25^{\circ} \mathrm{C}, \mathrm{t}_{\mathrm{p}}=10 \mu \mathrm{~s}$, Pulse |  |
| $\mathrm{P}_{\text {tot }}$ | Power Dissipation | $\begin{gathered} 136.3 \\ 59 \end{gathered}$ | W | $\begin{aligned} & \mathrm{T}_{\mathrm{C}}=25^{\circ} \mathrm{C} \\ & \mathrm{~T}_{\mathrm{C}}=110^{\circ} \mathrm{C} \end{aligned}$ |  |
| $\mathrm{T}_{\mathrm{j}}, \mathrm{T}_{\text {stg }}$ | Operating Junction and Storage Temperature | $\begin{gathered} -55 \text { to } \\ +175 \end{gathered}$ | ${ }^{\circ} \mathrm{C}$ |  |  |
|  | TO-220 Mounting Torque | $\begin{gathered} 1 \\ 8.8 \end{gathered}$ | $\underset{\substack{\mathrm{Nm} \\ \mathrm{lbf-in}}}{ }$ | M3 Screw 6-32 Screw |  |

## Electrical Characteristics

| Symbol | Parameter | Typ. | Max. | Unit | Test Conditions | Note |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $V_{F}$ | Forward Voltage | $\begin{aligned} & 1.5 \\ & 2.0 \end{aligned}$ | $\begin{aligned} & 1.8 \\ & 2.4 \end{aligned}$ | V | $\begin{aligned} & \mathrm{I}_{\mathrm{F}}=10 \mathrm{~A} \quad \mathrm{~T}_{\mathrm{J}}=25^{\circ} \mathrm{C} \\ & \mathrm{I}_{\mathrm{F}}=10 \mathrm{~A} \quad \mathrm{~T}_{\mathrm{J}}=175^{\circ} \mathrm{C} \end{aligned}$ |  |
| $\mathrm{I}_{\mathrm{R}}$ | Reverse Current | $\begin{aligned} & 10 \\ & 20 \end{aligned}$ | $\begin{gathered} 50 \\ 200 \end{gathered}$ | $\mu \mathrm{A}$ | $\begin{array}{ll} V_{R}=600 \vee & T_{J}=25^{\circ} \mathrm{C} \\ V_{R}=600 \vee & T_{j}=175^{\circ} \mathrm{C} \end{array}$ |  |
| $\mathrm{Q}_{\mathrm{C}}$ | Total Capacitive Charge | 25 |  | nC | $\begin{aligned} & \mathrm{V}_{\mathrm{R}}=600 \mathrm{~V}, \mathrm{I}_{\mathrm{F}}=10 \mathrm{~A} \\ & \mathrm{di} / \mathrm{d} t=500 \mathrm{~A} / \mu \mathrm{s} \\ & \mathrm{~T}_{\mathrm{J}}=25^{\circ} \mathrm{C} \end{aligned}$ |  |
| C | Total Capacitance | $\begin{gathered} 480 \\ 50 \\ 42 \end{gathered}$ |  | pF | $\begin{aligned} & V_{R}=0 \mathrm{~V}, \mathrm{~T}_{\mathrm{J}}=25^{\circ} \mathrm{C}, \mathrm{f}=1 \mathrm{MHz} \\ & \mathrm{~V}_{\mathrm{R}}=200 \mathrm{~V}_{1} \mathrm{~T}_{\mathrm{J}}=25^{\circ}{ }^{\circ} \mathrm{C}, \mathrm{f}=1 \mathrm{MHz} \\ & \mathrm{~V}_{\mathrm{R}}=400 \mathrm{~V}, \mathrm{~T}_{\mathrm{J}}=25^{\circ} \mathrm{C}, \mathrm{f}=1 \mathrm{MHz} \end{aligned}$ |  |

## Note:

1. This is a majority carrier diode, so there is no reverse recovery charge.

## Thermal Characteristics

| Symbol | Parameter | Typ. | Unit |
| :---: | :--- | :---: | :---: |
| $\mathrm{R}_{\text {өлС }}$ | Thermal Resistance from Junction to Case | 1.2 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

## Typical Performance



Figure 1. Forward Characteristics


Figure 2. Reverse Characteristics

## Typical Performance



Figure 3. Current Derating


Figure 4. Capacitance vs. Reverse Voltage


Figure 5. Transient Thermal Impedance


Figure 6. Power Derating

## Package Dimensions

Package TO-263-2


PIN 1 O

| POS | Inches |  | Millimeters |  |
| :---: | :---: | :---: | :---: | :---: |
|  | Min | Max | Min | Max |
| A | .396 | .406 | 10.058 | 10.312 |
| B | .297 | .303 | 7.544 | 7.696 |
| C | .057 | .063 | 1.448 | 1.600 |
| D | .237 | .243 | 6.015 | 6.167 |
| $\mathrm{E}^{*}$ | 0.00 | .070 | 0.00 | 1.778 |
| F | .048 | .062 | 1.219 | 1.575 |
| G | .100 TYP |  | 2.540 TYP |  |
| H | .335 | .345 | 8.509 | 8.763 |
| J | .028 | .034 | .711 | .864 |
| K | $2^{\circ}$ | $4^{\circ}$ | $2^{\circ}$ | $4^{\circ}$ |
| L | .170 | .180 | 4.318 | 4.572 |
| M | .048 | .052 | 1.219 | 1.321 |
| N | .595 | .615 | 15.113 | 15.621 |
| P | 0.00 | 0.10 | 0.00 | .254 |
| Q | R0.018 <br> TYP | R0.022 |  |  |
| TYP | R0.457 | RO.559 |  |  |
| R | .090 | .110 | 2.286 | 2.794 |
| S | .013 | .017 | .330 | .432 |
| T | $6.5^{\circ}$ | $8.5^{\circ}$ | $6.5^{\circ}$ | $8.5^{\circ}$ |
| U | .103 | .107 | 2.616 | 2.718 |
| V | R0. <br> TYP | R0.032 <br> TYP | R0.711 <br> TYP | R0.813 <br> TYP |
| W | - | $5.0^{\circ}$ | - | $5.0^{\circ}$ |

Note:

* Tab "E" may not be present

Recommended Solder Pad Layout


TO-263-2

| Part Number | Package | Marking |
| :---: | :---: | :---: |
| C3D10060G | TO-263-2 | C3D10060 |

## Diode Model



$$
\begin{gathered}
V f_{T}=V_{T}+I f * R_{T} \\
V_{T}=0.98+\left(T_{J} *-1.6 * 10^{-3}\right) \\
R_{T}=0.04+\left(T_{j} * 0.522^{*} 10^{-3}\right)
\end{gathered}
$$

Note: $\mathbf{T}_{\mathbf{j}}=$ Diode Junction Temperature In Degrees Celcius

 $2002 / 95 / E C$ on the restriction of the use of certain hazardous substances in electrical and electronic equipment (RoHS), as amended through April $21,2006$.

